

### Description

The DMN26D0UFB4-7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### **General Features**

$$\begin{split} V_{DS} &= 20V \ I_D = 0.7A \\ R_{DS(ON)} < 350 \ m\Omega @ \ V_{GS} = 4.5V \\ R_{DS(ON)} < 420 \ m\Omega @ \ V_{GS} = 2.5V \\ ESD = 2500V \ HBM \end{split}$$

### Application

Load/Power Switching Interfacing Switching Battery Management for Ultra Small Portable Electronics

### Package Marking and Ordering Information

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Product ID	Pack	Marking	Qty(PCS)	
DMN26D0UFB4-7	DFN1006-3L	34	10000	

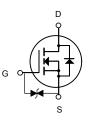
## Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Limit	Unit
Drain-Source Voltage	20	V
Gate-Source Voltage	±10	V
Drain Current-Continuous	0.7	А
Maximum Power Dissipation	0.15	W
Operating Junction and Storage Temperature Range	-55 To 150	°C
Thermal Resistance, Junction-to-Ambient (Note 2)	1250	°C <b>/W</b>
	Drain-Source Voltage         Gate-Source Voltage         Drain Current-Continuous         Maximum Power Dissipation         Operating Junction and Storage Temperature Range	Drain-Source Voltage20Gate-Source Voltage±10Drain Current-Continuous0.7Maximum Power Dissipation0.15Operating Junction and Storage Temperature Range-55 To 150

DMN26D0UFB4-7 N-Channel Enhancement Mode MOSFET



DFN100େL



N-Channel MOSFET



# DMN26D0UFB4-7

N-Channel Enhancement Mode MOSFET

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
STATIC CHARACTERISTICE						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250µA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> = 0V			1	μA
Gate-body leakage current	Igss	V <sub>GS</sub> =±10V, V <sub>DS</sub> = 0V			±10	μA
Gate threshold voltage (note2)	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA	0.45	0.7	1.1	V
Drain-source on-resistance (note2)		V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.5A		0.22	0.35	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.5A		0.28	0.42	Ω
Forward tranconductance (note2)	<b>g</b> fs	V <sub>DS</sub> =5.0V, I <sub>D</sub> =0.5A		1.6		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> =0.8A, V <sub>GS</sub> =0V			1.2	V
DYNAMIC CHARACTERISTICS (not	e4)			1		
Input capacitance	Ciss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V, f =1MHz		43.6		pF
Output capacitance	Coss			6.8		pF
Reverse transfer capacitance	Crss			4.6		pF
SWITCHING CHARACTERISTICS	(note4)			1		
Turn-on delay time (note3)	t <sub>d(on)</sub>			1.4		nS
Turn-on rise time (note3)	tr			27.8		nS
Turn-off delay time (note3)	t <sub>d(off)</sub>	V <sub>GS</sub> =4.5V,V <sub>DS</sub> =10V, R <sub>L</sub> =20Ω		54.6		nS
Turn-off fall time (note3)	tr			25.6		nS

## Electrical Characteristics (T<sub>A</sub> = 25 °C, unless otherwise specified)

Notes:

1. Surface mounted on FR4 board using the minimum recommended pad size.

2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.

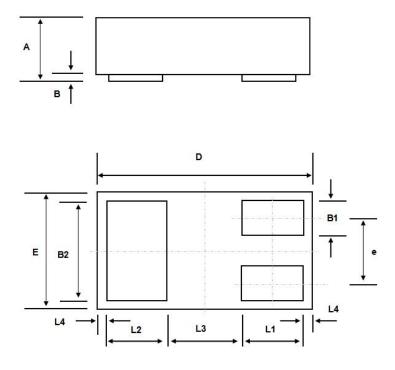
3. Switching characteristics are independent of operating junction temperatures.

4. Guaranteed by design, not subject to producting.



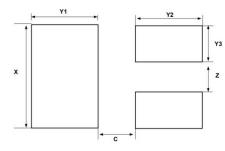
# **Package Outline Dimensions**

DFN1006-3L



Symbol	Dimensions In Millimet		
	Min	Max	
А	0.33	0.50	
В	0.00	0.05	
B1	0.10 0.20		
B2	0.45	0.55	
D	0.90	1.05	
Е	0.50 0.65		
е	0.35		
L1	0.20	0.30	
L2	0.20	0.30	
L3	0.39		
L4	0.05		

# Suggested Pad Layout (mm)



Symbol	Dimensions
С	0.25
х	0.65
Y1	0.50
Y2	0.50
Y3	0.25
Z	0.20



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